

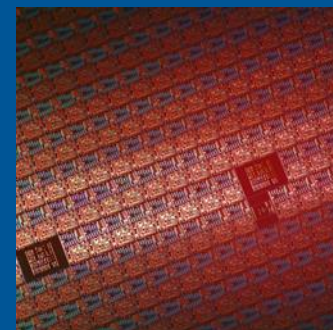


Accelerating the next technology revolution

2014 EUVL Symposium *Closing Address*

Stefan Wurm, SEMATECH
Patrick Naulleau, LBNL

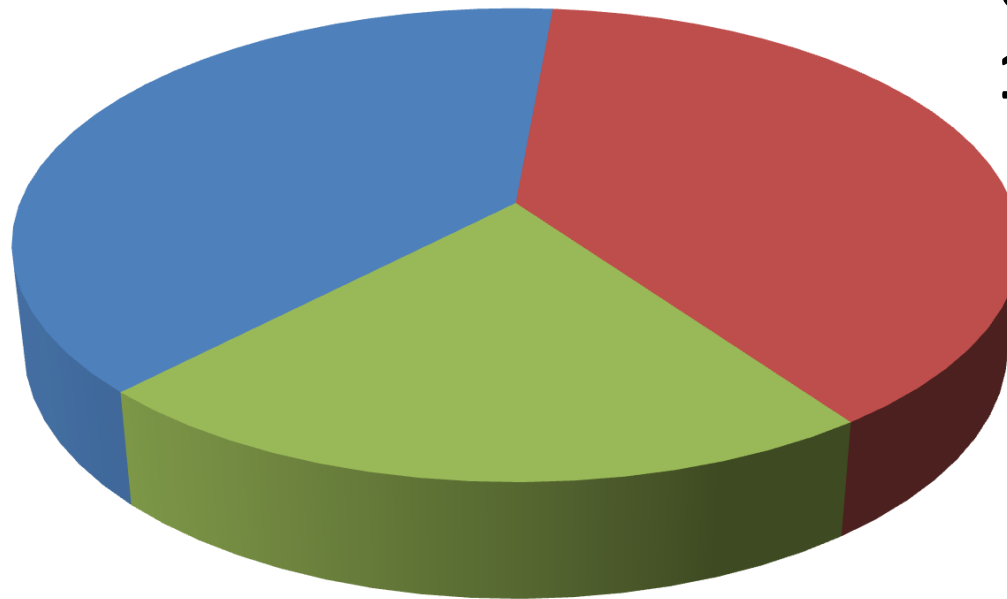
October, 29 2014



EUVL Symposium Attendance in 2014: By Geographic Region

Asia / Pacific
105 (39%)

United States
104 (39%)

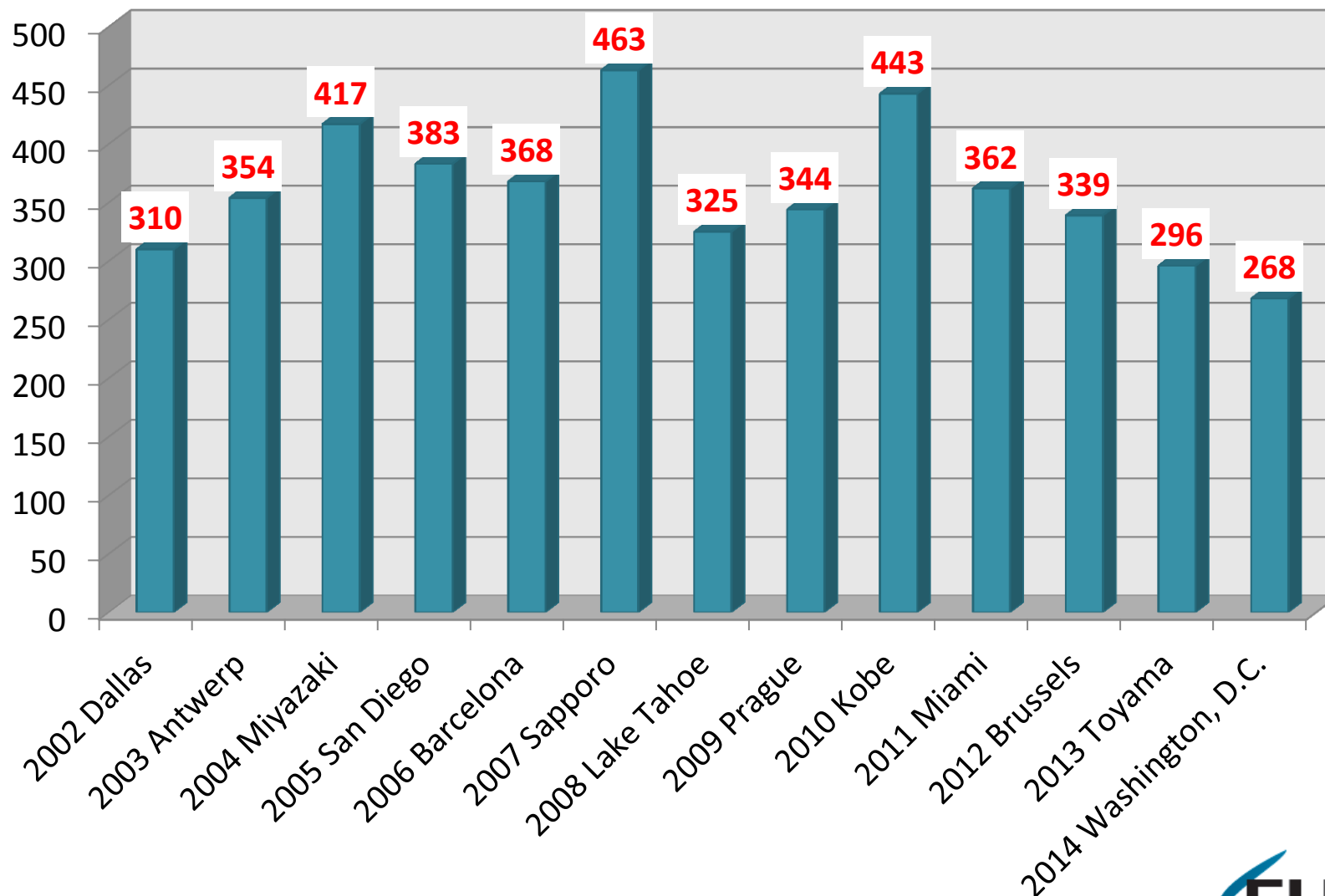


Europe
59 (22%)

268 Participants



EUVL Symposium Attendance by Year





Some Highlights

General Observations

- Overall, tone and outlook at the conference is positive: we are not out of the woods yet but we are on the right path (Tony Yen, TSMC)
- However, EUVL is under pressure to make significant progress over the next 12 months to become the irreversible (or reversible) 7 nm litho choice for leading edge foundry customers
- Anamorphic Lithography for high NA EUV – a major breakthrough for EUV Extendibility
 - Until recently it looked as if EUV would run out of nodes with 7 nm being seen as the last node where EUVL could be used in SP
 - The Anamorphic Lithography approach re-establishes EUVL as a multi-node technology

EUV Source

- 80W source power demonstrated in the field
 - Very encouraging that we do meet roadmap milestones as planned
 - Must meet 125W in 1H 2015
- Two customers demonstrate > 500 wafers/day on NXE3300

EUV Mask

- Actinic mask metrology tools (blank inspection and mask review) are coming online
 - Actinic patterned mask inspection remains an open challenge
- Mask blank defect reduction was demonstrated
 - Need to see this now at yield coming from commercial supply chain
 - Mask blank material supply could quickly become a bottle neck
- Pellicle membrane technology makes good progress but an industry integrated business strategy needs to be implemented

EUV Resist

- The general perception is that progress in resist materials improvement has stalled
 - There was little substantial progress over the last year
 - If not addressed, resist material readiness is at risk of quickly becoming a bottle neck for EUVL introduction
- A lot of excellent non-CAR materials research work is happening
 - This needs to quickly translate into supplier development of those new materials to drive them towards meeting manufacturing requirements



EUV Focus Areas

EUVL Focus Areas 2009-2013:

22 nm half-pitch insertion target



2009 / 22hp	2010 / 22hp	2011 / 22hp	2012 / 22hp	2013 / 22hp
1. Mask yield & defect inspection/review infrastructure	1. Mask yield & defect inspection/review infrastructure	1. Long-term reliable source operation with 200 W at IF*	1. Long-term reliable source operation with a. 200 W at IF in 2014 b. 500 W-1,000 W in 2016	1. Long-term reliable source operation with a. 125 W at IF in 2014 b. 250 W in 2015
2. Long-term reliable source operation with 200 W at IF	1. Long-term reliable source operation with 200 W at IF	2. Mask yield & defect inspection/review infrastructure	2. Mask yield & defect inspection/review infrastructure	2. Mask yield & defect inspection/review infrastructure
3. Resist resolution, sensitivity & LER met simultaneously	2. Resist resolution, sensitivity & LER met simultaneously	3. Resist resolution, sensitivity & LER met simultaneously	3. Resist resolution, sensitivity & LER met simultaneously	4. Keeping mask defect free – Availability of pellicle mtg HVM req't – Minimize defect adders during use
• EUVL manufacturing integration	• EUVL manufacturing integration	• EUVL manufacturing integration	• EUVL manufacturing integration	4. Resist resolution, sensitivity & LER met simultaneously

Ranked by 12th International EUVL Symposium Program Steering Committee. Toyama, Japan October 10, 2013

From 2013 Symposium



2014 EUVL Focus Areas



Key Focus Areas	Rank*	StdDev
Reliable source operation with > 75% availability <ul style="list-style-type: none"> - 125 W at IF in 1H / 2015 (at customer) - 250 W at IF in 1H / 2016 (HVM entry at customer) 	1.2	0.48
Resist resolution, sensitivity & LER met simultaneously <ul style="list-style-type: none"> - Progress insufficient to meet 2015 introduction target 	2.3	0.78
Mask yield & defect inspection/review infrastructure <ul style="list-style-type: none"> - Enable high yield defect free mask blank supply chain 	3.1	1.08
Keeping mask defect free <ul style="list-style-type: none"> - Availability of pellicle meeting HVM requirement – need integrated industry strategy for solution - Minimize defect adders during use 	3.3	0.89

Ranked by 13th International EUVL Symposium Program Steering Committee. Washington, D.C., October 29, 2014



**) Average of steering committee member votes*

EUVL Focus Areas 2012-2014



2012 / 22hp	2013 / 22hp	2014 / 16hp
1. Long-term reliable source operation with a. 200 W at IF in 2014 b. 500 W-1,000 W in 2016	1. Long-term reliable source operation with a. 125 W at IF in 2014 b. 250 W in 2015	1. Reliable source operation with > 75% availability – 125 W at IF in 1H / 2015 (at customer)) – 250 W at IF in 1H / 2016 (HVM entry at customer)
2. Mask yield & defect inspection/review infrastructure	2. Mask yield & defect inspection/review infrastructure	2. Resist resolution, sensitivity & LER met simultaneously – Progress insufficient to meet 2015 introduction target
3. Resist resolution, sensitivity & LER met simultaneously	4. Keeping mask defect free – Availability of pellicle mtg HVM req't – Minimize defect adders during use	3. Mask yield & defect inspection/review infrastructure – Enable high yield defect free mask blank supply chain
• EUVL manufacturing integration	4. Resist resolution, sensitivity & LER met simultaneously	3. Keeping mask defect free – Availability of pellicle mtg HVM req't : need integrated industry strategy for solution – Minimize defect adders during use

Ranked by 13th International EUVL Symposium Program Steering Committee, Washington, D.C. October 29, 2014





2015 EUVL Symposium Announcement

K. Ronse, E. Hendrickx



ANNOUNCEMENT 1

EUV SYMPOSIUM 2015

K. RONSE, E. HENDRICKX

ANNOUNCEMENT 1

29 OCTOBER 2014



FOCUS POINTS EUVS 2015

► Day 1 :

EUV readiness :

- Will EUVL meet the N7 insertion deadline ?
(invited speakers, NXE:3300 users)

► Day 2-3 :

EUV extendibility :

- Progress on EUV (alternative) resist materials
- Progress EUV alternative mask architectures
- Progress EUV pellicles and implementation
- Progress EUV reticle inspection
- Progress EUV high power sources
- Progress high NA EUV anamorphic

DATE AND ORGANIZATION

The next EUVL symposium will be held in Europe :

week of 4-7 October 2015

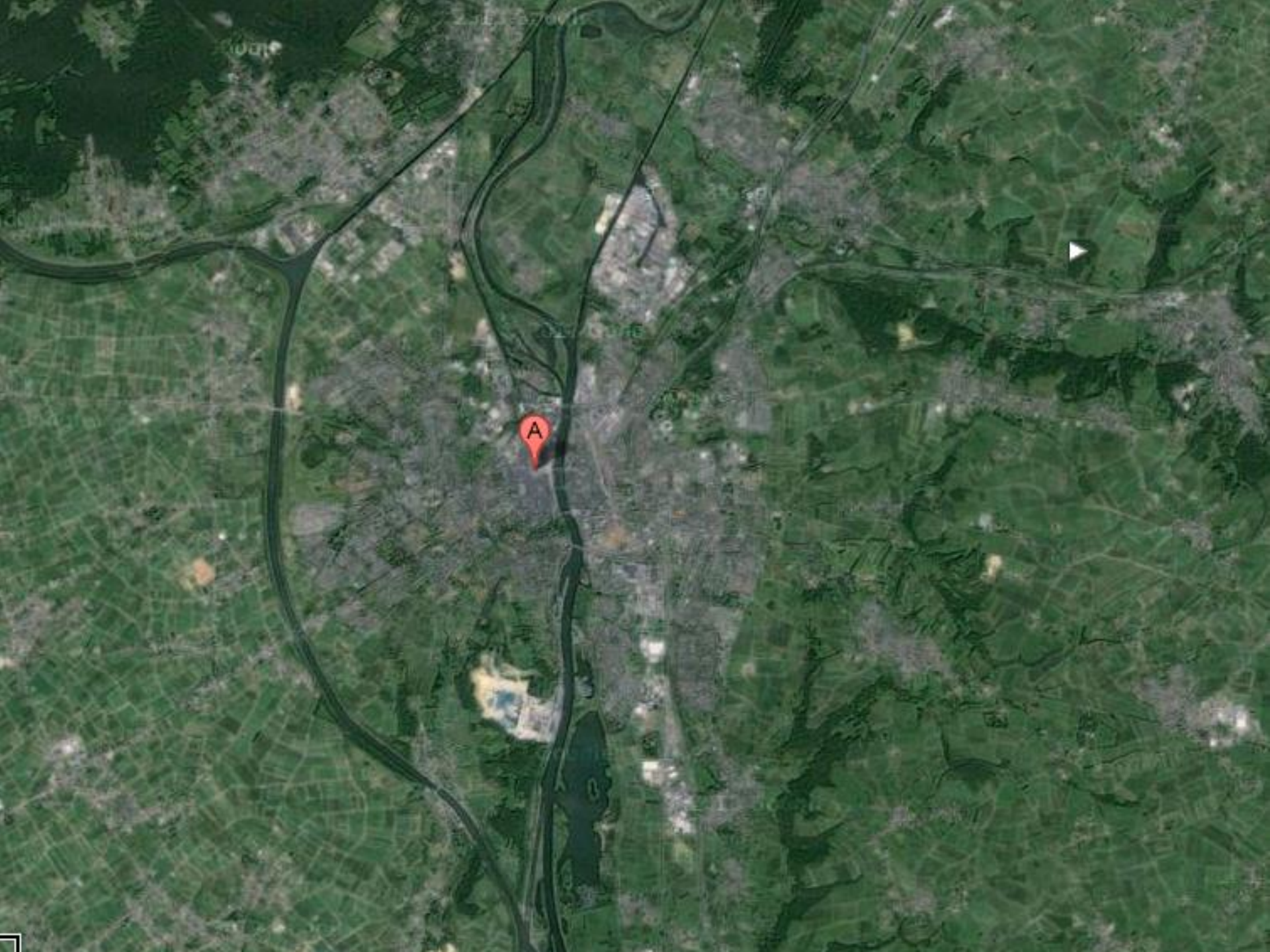
organized by imec, in cooperation with SEMATECH and EIDEC

Symposium Chair : Kurt Ronse

Program Chair : Eric Hendrickx







LOCATION : MAASTRICHT (NL)









MAASTRICHT



MAASTRICHT

HOW TO REACH ?

- ▶ 2 major airports at $\approx 100\text{km}$ from Maastricht
 - Brussels International Airport (Belgium)
 - Dusseldorf International airport (Germany)
- ▶ Public transport from airport to MECC
 - Trains
 - Bus shuttle service (being considered)

CONFERENCE CENTER MECC



CONFERENCE CENTER MECC



CONFERENCE CENTER MECC



CONFERENCE CENTER MECC



CONFERENCE CENTER MECC



CONFERENCE CENTER MECC



ACCOMMODATION : NH MAASTRICHT HOTEL



87,00USD/night

- ▶ Free buses connect city center with MECC
- ▶ Other hotel options in city center

MARK YOUR CALENDARS !!!

4-7 October 2015



**ASPIRE
INVENT
ACHIEVE**



IMEC



Best Poster / Best Presentation

International Symposium on Extreme Ultraviolet Lithography

October 27-29, 2014 • Washington, D.C.



2014 EUVL Symposium Best Poster Presentation

Excellence Award

Presented to

Antoine Wojdyla
Berkeley Lab

*Fourier Ptychography Microscopy with SHARP EUV Microscope for Increased
Imaging Resolution Based on Illumination Diversity*



International Symposium on Extreme Ultraviolet Lithography

October 27-29, 2014 • Washington, D.C.



2014 EUVL Symposium Best Paper Presentation

Excellence Award

Presented to

Sascha Migura
Carl Zeiss SMT GmbH

EUV Lithography Optics for sub 9nm Resolution





Thank you & Symposium Dinner

International Symposium on Extreme Ultraviolet Lithography

October 27-29, 2014 • Washington, D.C.



2014 EUVL Symposium Sponsors – Thank You!



ASML



ENERGETIQ



euv tech



FUJIFILM
Value from Innovation



HITACHI
Inspire the Next

JSR Micro
MATERIALS INNOVATION

Lasertec



optiXfab.



SYNOPSYS



tok

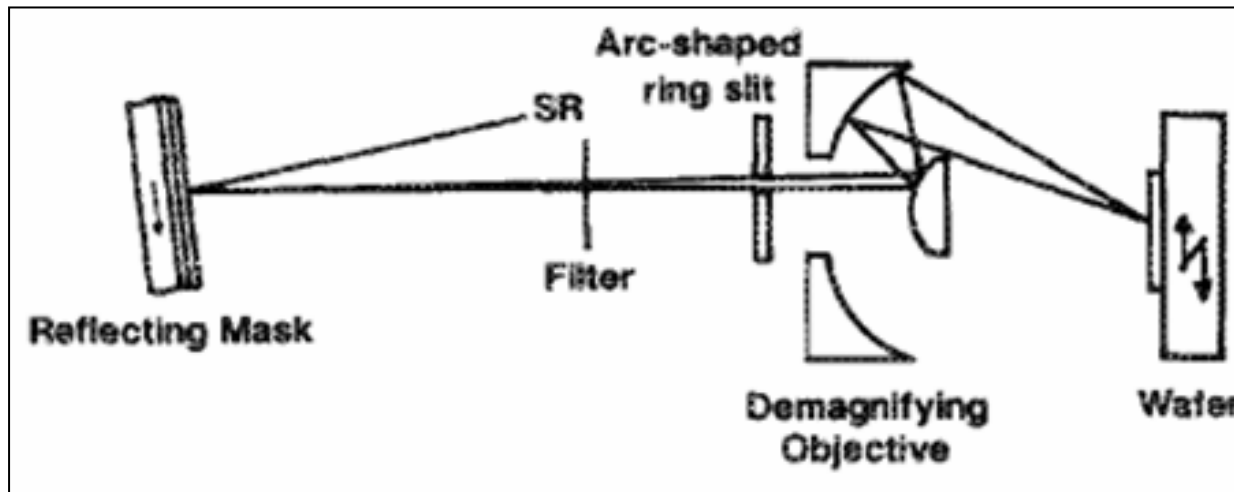


Thank you!

- Symposium co-chairs:
Toshiro Itani (EIDEC), Kurt Ronse (imec)
- Program co-committee:
Patrick Naulleau
Soichi Inoue (EIDEC), Winfried Kaiser (Carl Zeiss)
All abstract reviewers
- Program logistics / support
Marcy DeBiccary, Kelly Abbruzzese
Our session chairs
- All paper / poster presenters
With special thanks to our keynote and invited speakers

Thank you to an EUVL Pioneer!

Prof. Dr. Hiroo Kinoshita



Symposium Dinner

- Buses will leave at 6:30 PM
- Parkview Entrance of hotel
 - Lobby level, East Side
- Please have your name badge (if possible) to check-in prior to boarding the bus